

# PROCEEDINGS OF SPIE

## ***Design for Manufacturability through Design-Process Integration II***

**Vivek K. Singh**  
**Michael L. Rieger**  
*Editors*

**28–29 February 2008**  
**San Jose, California, USA**

*Sponsored by*  
SPIE

*Cooperating Organization*  
SEMATECH (USA)

*Published by*  
SPIE

**Volume 6925**

Proceedings of SPIE, 0277-786X, v. 6925

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Please use the following format to cite material from this book:

Author(s), "Title of Paper," in *Design for Manufacturability through Design-Process Integration II*, edited by Vivek K. Singh, Michael L. Rieger, Proceedings of SPIE Vol. 6925 (SPIE, Bellingham, WA, 2008) Article CID Number.

ISSN 0277-786X  
ISBN 9780819471109

Published by

**SPIE**

P.O. Box 10, Bellingham, Washington 98227-0010 USA  
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445  
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Printed in the United States of America.

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